

OEM Silicon Pressure Die

AccuStable[™] SM30G Platinum Family

FEATURES

- Platinum bond-pads enable use in harsh environments
- Qualified using Grade 0 AEC-Q100 automotive standards
- Enhanced stability with an integrated field shield
- Extended operating temperature range: -40°C to 150°C
- Small size 1.35 x 1.35 mm
- <1% Output shift over life
- Differential or gage configuration
- Available 5, 15, & 30 PSI
- Ratiometric with supply voltage up to 10 V
- Manufactured according to ISO9001 and ISO/TS 16949 standards
- RoHS & REACH compliant



DESCRIPTION

The SM30G-Platinum is a silicon micro-machined, piezoresistive pressure sensing die. This device will be available with a full-scale range of 5 to 30 PSI and is ideal for OEM and high-volume applications. The device has platinum bond-pads to enable its use in harsh environments.

Provided in die form, these sensors can be mounted on ceramic on a variety of substrates or packages as part of an OEM system. They also may be packaged into proprietary or application specific sensor lines.

The devices are electrically probed, diced, inspected and shipped on tape. Electronic wafer maps are provided with each wafer.

| Medical | Industrial | Automotive |
|-------------------------|---------------------|---------------------------------|
| Patient Monitors | Industrial Controls | Diesel Particulate Filter (DPF) |
| Blood Pressure Monitors | Compressors & Pumps | Exhaust Gas Recirculation (EGR) |
| Oxygen Concentrators | Pressure Switches | Automotive Systems |
| Fluid Evacuation | | Gas Particulate Filter (GPF) |



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Absolute Maximum Ratings

| No. | Characteristic | Symbol | Minimum | Typical | Maximum | Units |
|-----|------------------------------------|------------------|---------|---------|---------|-------|
| 1 | Excitation Voltage ^(a) | V _{DD} | - | - | 10 | V |
| 2 | Operating Temperature | Τ _{ΟΡ} | -40 | - | +150 | °C |
| 3 | Storage Temperature ^(a) | T _{stg} | -55 | - | +150 | °C |
| 4 | ESD Rating - Human Body Model | V _{ESD} | | | 2 | kV |

Notes:

a. The device can only be driven with the supply voltage connected to the pins as shown.

| No. | Product Number | Legacy Product Number | Operating Pressure ^(c) | Proof Pressure (P _{PROOF}) ^(b) | Burst Pressure (P _{BURST}) ^(b) |
|-----|-----------------------|--------------------------|--|--|--|
| 5 | SM30G-H-ND-005S-0010A | SM3022-005-G-D | ±5 PSI 0 to 5 PSI 0 to -5 PSI | 25 PSI | 40 PSI |
| 6 | SM30G-H-ND-015S-0010A | SM3022-015-G-D | ±15 PSI 0 to 15 PSI 0 to -15 PSI | 45 PSI | 75 PSI |
| 7 | SM30G-H-ND-030S-0010A | SM3022-030-G-D | ±30 PSI 0 to 30 PSI 0 to -30 PSI | 90 PSI | 150 PSI |

Notes:

b. Tested on a sample basis. The burst and proof pressure values are limited by pressure applied to the backside of the die. The burst and proof pressure values are higher than shown here when pressure is applied to the topside of the die.

c. Can be operated as topside gauge, backside gage & differential.



OPERATING CHARACTERISTICS FOR SM30G Platinum Series

The operating characteristics are based on packaged die. The sensor performance may vary depending on the die attach material and process. The die attach material and process should minimize the stress transferred to the sensor die.

The sensor can be operated with the highest pressure applied to the topside of the die (topside operation) or the highest pressure applied to the backside of the die (backside operation). With topside operation, increasing topside pressure will result in an increasing sensor output.

Operating Characteristics - Specifications

All parameters are specified at Vdd = 5.0 V supply voltage at 25°C, unless otherwise noted.

| No. | . Characteristic | | Symbol | Minimum | Typical | Maximum | Units |
|-----|--|-----------------------------|-------------------|---------|---------|---------|-------|
| 8 | Topside | 5, 15 PSI ^(c, d) | | 60 | 90 | 120 | mV |
| 0 | Span (FS P _{RANGE}) | 30 PSI ^(c, d) | V _{SPAN} | 55 | 80 | 105 | |
| 9 | Backside 5, 15 PSI ^(c, d) | V | 60 | 90 | 120 | | |
| 9 | Span (FS P _{RANGE}) | 30 PSI ^(c, d) | V _{SPAN} | 55 | 80 | 105 | mV |
| 10 | Zero Offset | | V _{ZERO} | -45 | -5 | +25 | mV |
| 11 | TC Span ^(c, e, f) | | TCS | -0.24 | -0.19 | -0.155 | %/°C |
| 12 | TC Zero Offset ^(c, e, f) | | TCZ | -75 | - | 75 | μV/°C |
| 13 | TC Resistance ^(c, e, f) | | TCR | 0.24 | 0.275 | 0.33 | %/°C |
| 14 | Linearity - Topside ^(c, f, g) | | NL _{TS} | -0.15 | <±0.10 | 0.15 | %/FS |
| 15 | Linearity Deckeide | 5 PSI ^(c, f, h) | NL _{BS} | -0.3 | <±0.2 | 0.3 | %/FS |
| 15 | Linearity – Backside | 15, 30 ^(c, f, h) | | -0.15 | <±0.10 | 0.15 | |
| 16 | Bridge Resistance | | R _B | 4 | 5 | 6 | kΩ |
| 17 | Pressure Hysteresis ^(c) | | P _{HYS} | | <±0.1 | | %FS |
| 18 | Thermal Hysteresis ^(c, e) | | T _{HYS} | | <±0.3 | | %FS |

Notes:

c. Tested on a sample basis

d. For other pressures, please contact SMI sales at +1-(408) 577-0100 or email at sales@si-micro.com

e. Determined by measurements taken over -40°C to 150°C

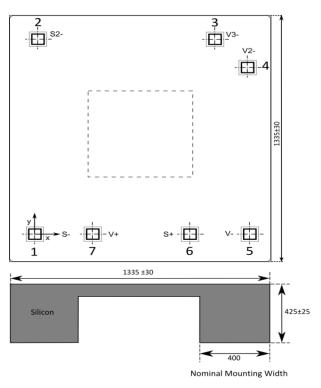
f. Defined as best fit straight line

g. Topside linearity is with the highest pressure applied to the topside of the die

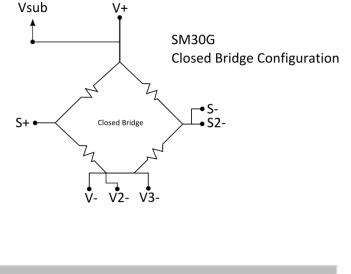
h. Backside linearity is with the highest pressure applied to the backside of the die



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SM30G Diagrams and Dimensions



Assembly Recommendations

(a) Use soft RTV for die-attachment
(b) A bond line thickness of 180-220 μm is recommended
(c) The RTV should not go up the inside of the die cavity by more than 50% of the die thickness.

Platinum bond-pad size = 110x110µm

All dimensions are in micron.

| Typical Operation | | | | | | |
|-------------------|-------------------------|-----------|-----------------|-------|------------------------|------------------------|
| PAD # | PAD DESCRIPTION | PAD LABEL | ТҮРЕ | VALUE | Coordinate X-Axis (µm) | Coordinate Y-Axis (µm) |
| 1 | Negative Sensor Output | S- | - Analog Output | - | 0 | 0 |
| 2 | Negative Sensor Output | S2- | - Analog Output | - | 0 | 1100 |
| 3 | Negative Supply Voltage | V3- | Power | 0 V | 890 | 1100 |
| 4 | Negative Supply Voltage | V2- | Power | 0 V | 1100 | 890 |
| 5 | Negative Supply Voltage | V- | Power | 0 V | 1100 | 0 |
| 6 | Positive Sensor Output | S+ | + Analog Output | - | 840 | 0 |
| 7 | Positive Supply Voltage | V+ | Power | +5 V | 260 | 0 |

NOTES:

• Closed bridge configuration: Pads 3, 4, & 5 are connected

• Open bridge configuration: Pads 4 & 5 are connected, and pad 3 is the second negative supply voltage connection



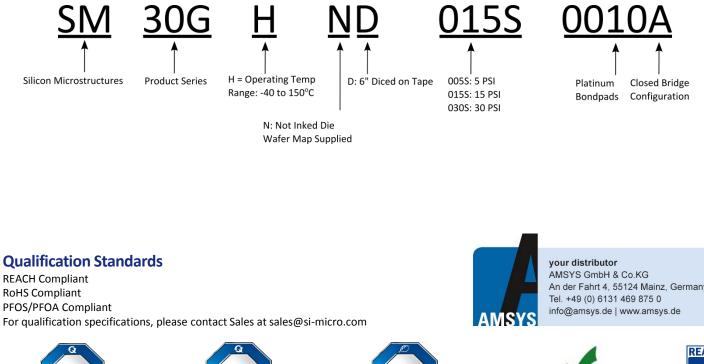
Ordering Information

| Order Code | Legacy Product Number | Configuration | Full-Scale Pressure Range* | Minimum Order Quantity |
|-----------------------|--------------------------|---------------|-------------------------------|--------------------------------|
| SM30G-H-ND-005S-0010A | SM3022-005-G-D | Closed Bridge | 5 PSI | |
| SM30G-H-ND-015S-0010A | SM3022-015-G-D | Closed Bridge | 15 PSI | 1 Wafer (1 wafer = 6,000 ±10%) |
| SM30G-H-ND-030S-0010A | SM3022-030-G-D | Closed Bridge | 30 PSI | |

NOTE: Part numbers of engineering samples are subject to change

* Topside 0 to +5 PSI, 0 to -5 PSI or ± FS Pressure

Part Number Legend









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